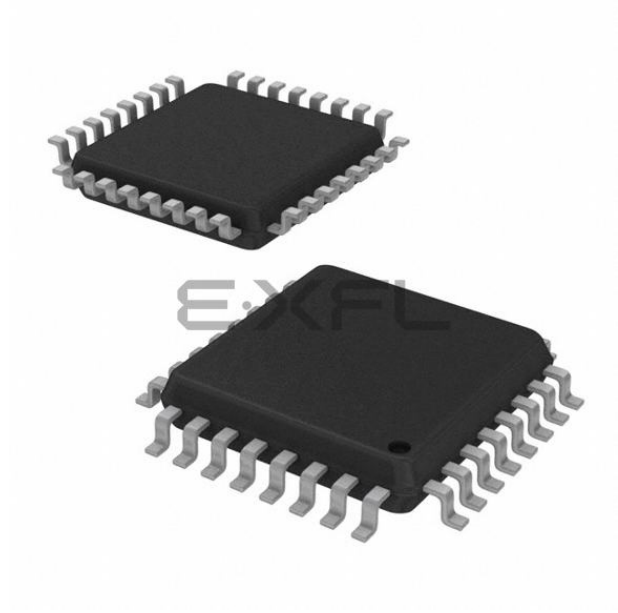

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	29
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 21x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8al3l46tay

List of tables

1 Introduction

This document describes the features, pinout, mechanical data and ordering information of the medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x devices (microcontrollers with up to 32-Kbyte Flash memory density). These devices are referred to as medium-density devices in STM8L051/L052 Value Line, STM8L151/L152, STM8L162, STM8AL31, STM8AL3L MCU lines reference manual (RM0031) and in STM8L and STM8AL Flash programming manual (PM0054).

For more details on the whole STMicroelectronics ultra-low-power family please refer to *Section 3: Functional overview on page 13*.

For information on the debug module and SWIM (single wire interface module), refer to the STM8 SWIM communication protocol and debug module user manual (UM0470).

For information on the STM8 core, please refer to the STM8 CPU programming manual (PM0044).

Note: The medium-density devices provide the following benefits:

- Integrated system
  - Up to 32 Kbytes of medium-density embedded Flash program memory
  - 1 Kbytes of data EEPROM
  - Internal high speed and low-power low speed RC.
  - Embedded reset
- Ultra-low power consumption
  - 195 µA/MHZ + 440 µA (consumption)
  - 0.9 µA with LSI in Active-halt mode
  - Clock gated system and optimized power management
  - Capability to execute from RAM for Low power wait mode and Low power run mode
- Advanced features
  - Up to 16 MIPS at 16 MHz CPU clock frequency
  - Direct memory access (DMA) for memory-to-memory or peripheral-to-memory access.
- Short development cycles
  - Application scalability across a common family product architecture with compatible pinout, memory map and modular peripherals.
  - Wide choice of development tools

All devices offer 12-bit ADC, DAC, two comparators, Real-time clock three 16-bit timers, one 8-bit timer as well as standard communication interface such as SPI, I2C and USART. A 4x28-segment LCD is available on the medium-density STM8AL3Lxx line. *Table 2: Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x low-power device features and peripheral counts* and *Section 3: Functional overview* give an overview of the complete range of peripherals proposed in this family.

Figure 1 shows the general block diagram of the device family.

2.1 Device overview

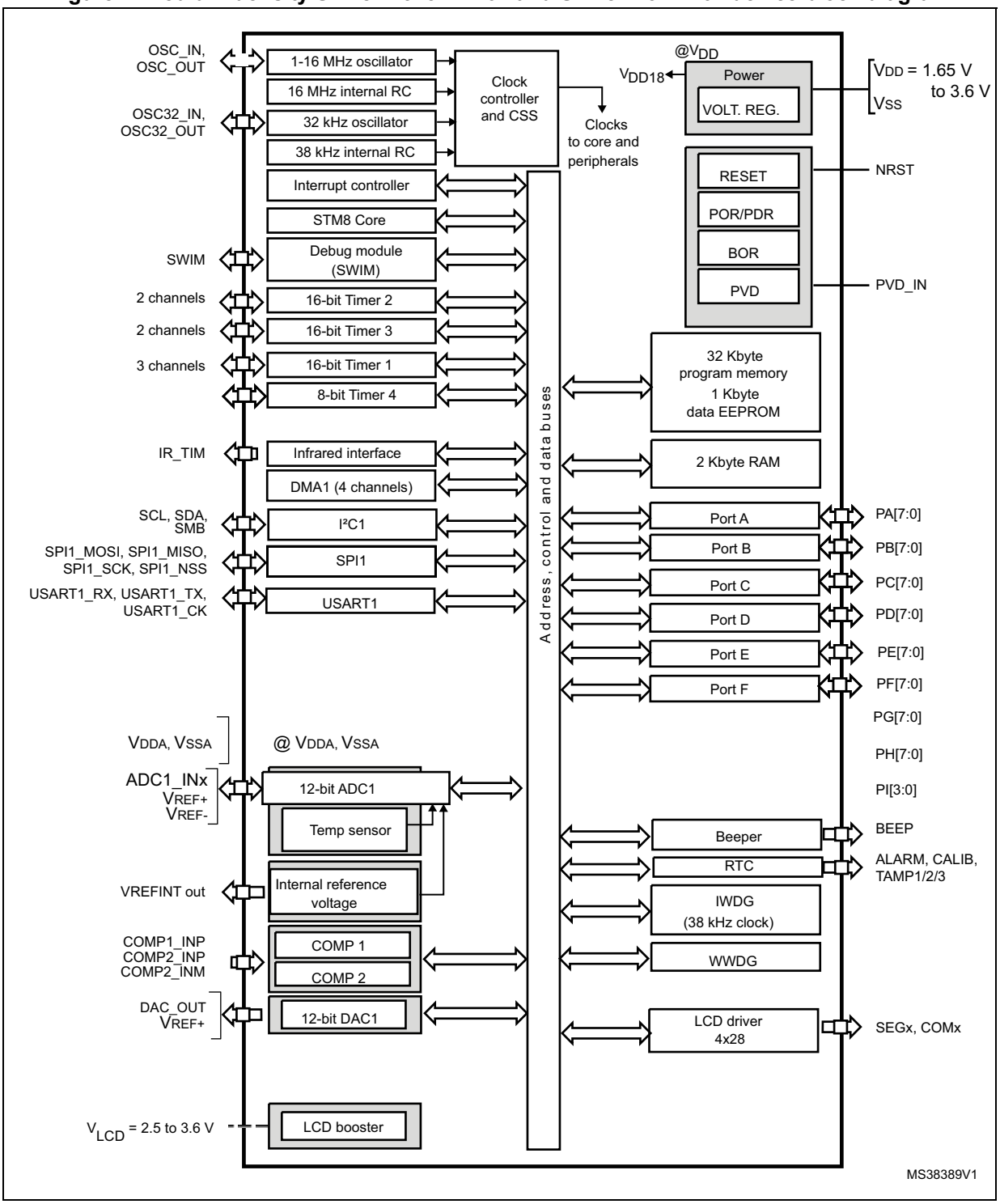
Table 2. Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x low-power device features and peripheral counts

Features		STM8AL3xx6			STM8AL3xx8		
Flash (Kbyte)		8	16	32	8	16	32
Data EEPROM (Kbyte)		1					
RAM-Kbyte		2			2		
LCD		4x17 (1)			4x28 (1)		
Timers	Basic	1 (8-bit)			1 (8-bit)		
	General purpose	2 (16-bit)			2 (16-bit)		
	Advanced control	1 (16-bit)			1 (16-bit)		
Communication interfaces	SPI	1			1		
	I2C	1			1		
	USART	1			1		
GPIOs		30 (2)(3) or 29 (1)(3)			41(3)		
12-bit synchronized ADC (number of channels)		1 (22 (2) or 21 (1))			1 (25)		
12-Bit DAC (number of channels)		1 (1)			1 (1)		
Comparators COMP1/COMP2		2			2		
Others		RTC, window watchdog, independent watchdog, 16-MHz and 38-kHz internal RC, 1- to 16-MHz and 32-kHz external oscillator					
CPU frequency		16 MHz					
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power down)					
Operating temperature		-40 to +85 °C/-40 to +125 °C					
Packages		LQFP32 (7 x7 mm) VFQFPN32 (5 x 5 mm)			LQFP48 (7x7) VFQFPN32 (5 x 5 mm)		

1. STM8AL3Lxx versions only
2. STM8AL31xx versions only
3. The number of GPIOs given in this table includes the NRST/PA1 pin but the application can use the NRST/PA1 pin as general purpose output only (PA1).

3 Functional overview

Figure 1. Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x device block diagram



1. **Legend**: ADC (Analog-to-digital converter), BOR (Brownout reset), DMA (Direct memory access), DAC (Digital-to-analog converter), I²C (Inter-integrated circuit multimaster interface), IWDG (Independent watchdog), LCD (Liquid crystal display), POR/PDR (Power on reset / power down reset), RTC (Real-time clock), SPI (Serial peripheral interface), SWIM (Single wire interface module), USART (Universal synchronous asynchronous receiver transmitter), WWDG (Window watchdog).

3.2 Central processing unit STM8

3.2.1 Advanced STM8 core

The 8-bit STM8 core is designed for code efficiency and performance with an Harvard architecture and a 3-stage pipeline.

It contains six internal registers which are directly addressable in each execution context, 20 addressing modes including indexed indirect and relative addressing, and 80 instructions.

Architecture and registers

- Harvard architecture
- 3-stage pipeline
- 32-bit wide program memory bus - single cycle fetching most instructions
- X and Y 16-bit index registers - enabling indexed addressing modes with or without offset and read-modify-write type data manipulations
- 8-bit accumulator
- 24-bit program counter - 16 Mbyte linear memory space
- 16-bit stack pointer - access to a 64 Kbyte level stack
- 8-bit condition code register - 7 condition flags for the result of the last instruction

Addressing

- 20 addressing modes
- Indexed indirect addressing mode for lookup tables located anywhere in the address space
- Stack pointer relative addressing mode for local variables and parameter passing

Instruction set

- 80 instructions with 2-byte average instruction size
- Standard data movement and logic/arithmetic functions
- 8-bit by 8-bit multiplication
- 16-bit by 8-bit and 16-bit by 16-bit division
- Bit manipulation
- Data transfer between stack and accumulator (push/pop) with direct stack access
- Data transfer using the X and Y registers or direct memory-to-memory transfers

3.2.2 Interrupt controller

The medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x feature a nested vectored interrupt controller:

- Nested interrupts with 3 software priority levels
- 32 interrupt vectors with hardware priority
- Up to 40 external interrupt sources on 11 vectors
- Trap and reset interrupts

9 Electrical parameters

9.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

9.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = -40 °C, T_A = 25 °C, and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production.

9.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3 V. They are given only as design guidelines and are not tested.

Typical ADC and DAC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range.

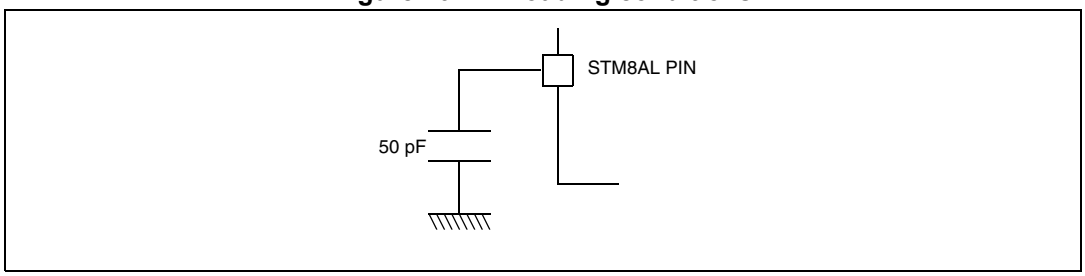
9.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

9.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

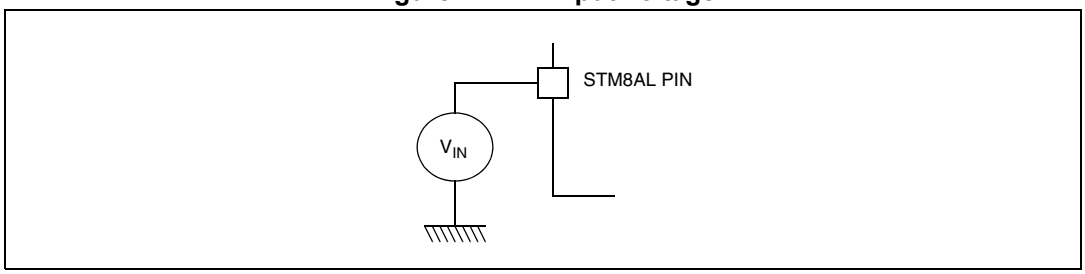
Figure 10. Pin loading conditions



9.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 11. Pin input voltage



9.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 15: Voltage characteristics*, *Table 16: Current characteristics* and *Table 17: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and a functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect the device's reliability.

The device's mission profile (application conditions) is compliant with the JEDEC JESD47 qualification standard, extended mission profiles are available on demand.

Table 15. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD}- V_{SS}	External supply voltage (including V_{DDA} and V_{DD2})(1)	- 0.3	4.0	V
V_{IN}(2)	Input voltage on true open-drain pins (PC0 and PC1)	V_{SS} - 0.3	V_{DD} + 4.0	
	Input voltage on five-volt tolerant (FT) pins (PA7 and PE0)			
	Input voltage on 3.6 V tolerant (TT) pins		4.0	
	Input voltage on any other pin			
V_{ESD}	Electrostatic discharge voltage	see *Absolute maximum ratings (electrical sensitivity) on page 106*		V

1. All power (V_{DD1}, V_{DD2}, V_{DDA}) and ground (V_{SS1}, V_{SS2}, V_{SSA}) pins must always be connected to the external power supply.
2. V_{IN} maximum must always be respected. Refer to *Table 16* for maximum allowed injected current values.

9.3 Operating conditions

Subject to general operating conditions for V_{DD} and T_A.

9.3.1 General operating conditions

Table 19. General operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
f_{SYSCLK}(1)	System clock frequency	1.65 V ≤ V_{DD} < 3.6 V		0	16	MHz
V_{DD}	Standard operating voltage	-		1.65(2)	3.6	V
V_{DDA}	Analog operating voltage	ADC and DAC not used	Must be at the same potential as V_{DD}	1.65(2)	3.6	V
		ADC and DAC used		1.8	3.6	V
P_D(3)	Power dissipation at T_A= 85 °C for suffix A devices	LQFP48		-	288	mW
		LQFP32		-	288	
		VFQFPN32		-	322	
	Power dissipation at T_A= 125 °C for suffix C devices	LQFP48		-	77	
		LQFP32		-	85	
		VFQFPN32		-	80	
T_A	Temperature range	1.65 V ≤ V_{DD} < 3.6 V (A suffix version)		-40	85	°C
		1.65 V ≤ V_{DD} < 3.6 V (C suffix version)		-40	125	
T_J	Junction temperature range	-40 °C ≤ T_A < 85 °C (A suffix version)		-40	105	°C
		-40 °C ≤ T_A < 125 °C (C suffix version)		-40	130	

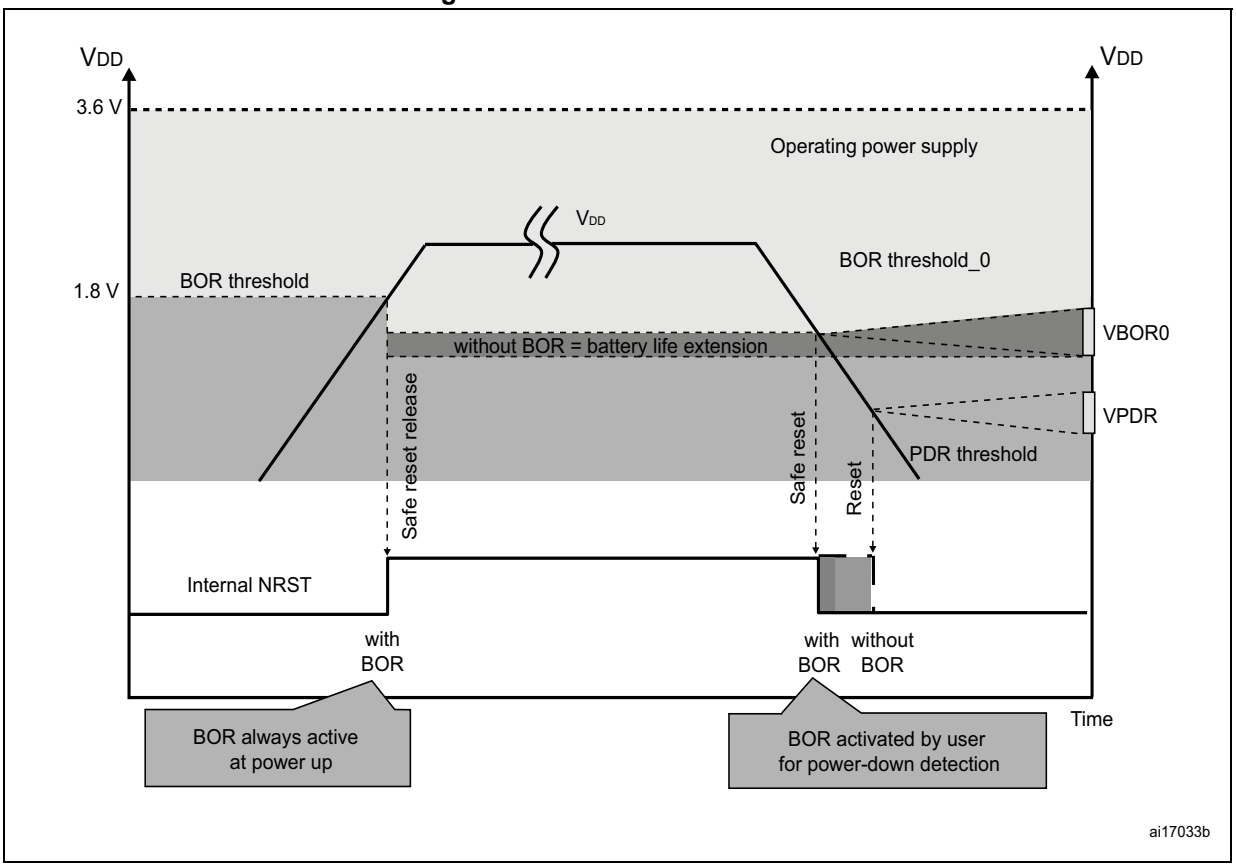
1. $f_{SYSCLK} = f_{CPU}$
2. 1.8 V at power-up, 1.65 V at power-down if BOR is disabled
3. To calculate $P_{Dmax}(T_A)$, use the formula $P_{Dmax}=(T_{Jmax} - T_A)/\Theta_{JA}$ with T_{Jmax} in this table and Θ_{JA} in “Thermal characteristics” table.

9.3.2 Embedded reset and power control block characteristics

Table 20. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	BOR detector enabled	0(1)	-	∞(1)	µs/V
	V_{DD} fall time rate	BOR detector enabled	20(1)	-	∞(1)	
t_{TEMP}	Reset release delay	V_{DD} rising	-	3	-	ms

Figure 12. POR/BOR thresholds



HSE crystal/ceramic resonator oscillator

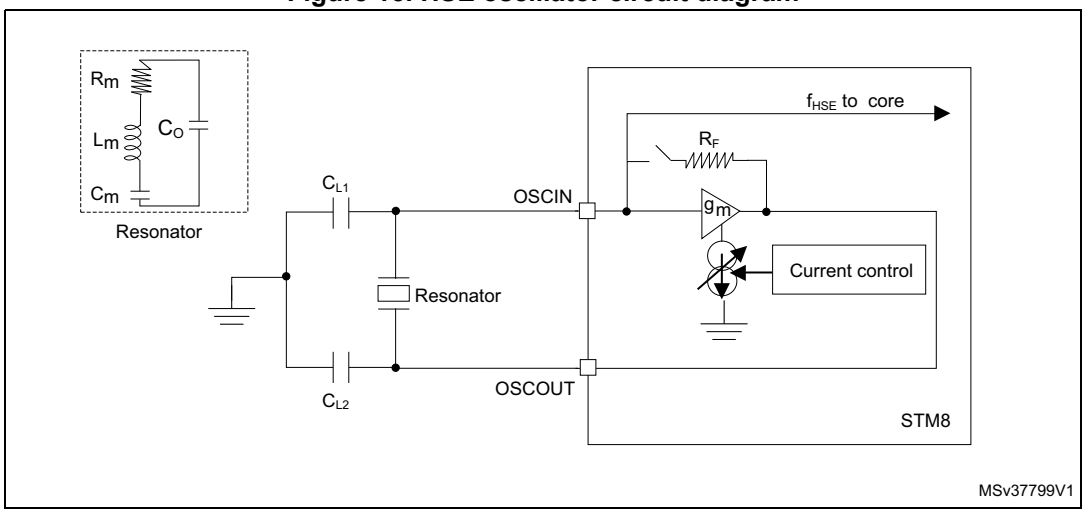
The HSE clock can be supplied with a 1 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 32. HSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE}	High speed external oscillator frequency	-	1	-	16	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
$C^{(1)}$	Recommended load capacitance $^{(2)}$	-	-	20	-	pF
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF, f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)$^{(3)}$	mA
		C = 10 pF, f_{OSC} =16 MHz	-	-	2.5 (startup) 0.46 (stabilized)$^{(3)}$	
g_m	Oscillator transconductance	-	3.5$^{(3)}$	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	1	-	ms

1. $C=C_{L1}=C_{L2}$ is approximately equivalent to 2 x crystal C_{LOAD}.
2. The oscillator selection can be optimized in terms of supply current using a high quality resonator with small R_m value. Refer to crystal manufacturer for more details
3. Guaranteed by design.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 16 MHz oscillation. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Figure 15. HSE oscillator circuit diagram



HSE oscillator critical g_m formula

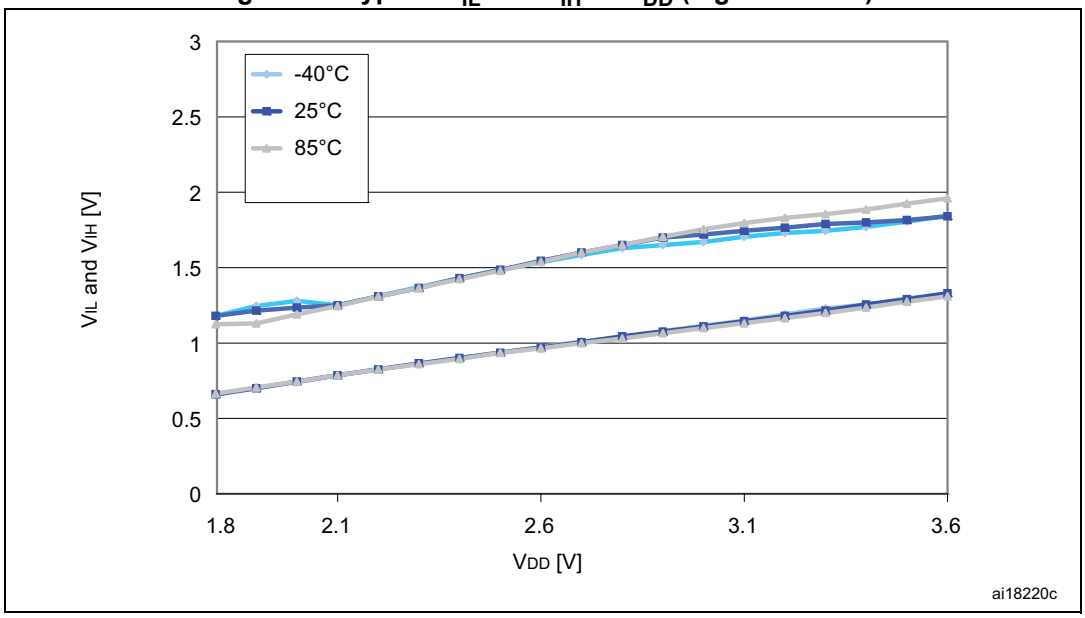
$$g_{mcrit} = (2 \times \Pi \times f_{HSE})^2 \times R_m(2Co + C)^2$$

Table 41. I/O static characteristics (continued)

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(5)	$V_{IN} = V_{SS}$	30(6)	45	60(6)	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. V_{DD} = 3.0 V, T_A = -40 to 125 °C unless otherwise specified.
2. If V_{IH} maximum cannot be respected, the injection current must be limited externally to $I_{INJ(PIN)}$ maximum.
3. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. R_{PU} pull-up equivalent resistor based on a resistive transistor (corresponding I_{PU} current characteristics described in *Figure 22*).
6. Data not tested in production.

Figure 19. Typical V_{IL} and V_{IH} vs V_{DD} (high sink I/Os)



Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 42. Output driving current (high sink ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
High sink	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +2 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +2 mA, V_{DD} = 1.8 V	-	0.45	
			I_{IO} = +10 mA, V_{DD} = 3.0 V	-	0.7	
	V_{OH} (2)	Output high level voltage for an I/O pin	I_{IO} = -2 mA, V_{DD} = 3.0 V	V_{DD}-0.45	-	V
			I_{IO} = -1 mA, V_{DD} = 1.8 V	V_{DD}-0.45	-	
			I_{IO} = -10 mA, V_{DD} = 3.0 V	V_{DD}-0.7	-	

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.

Table 43. Output driving current (true open drain ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Open drain	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +3 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +1 mA, V_{DD} = 1.8 V	-	0.45	

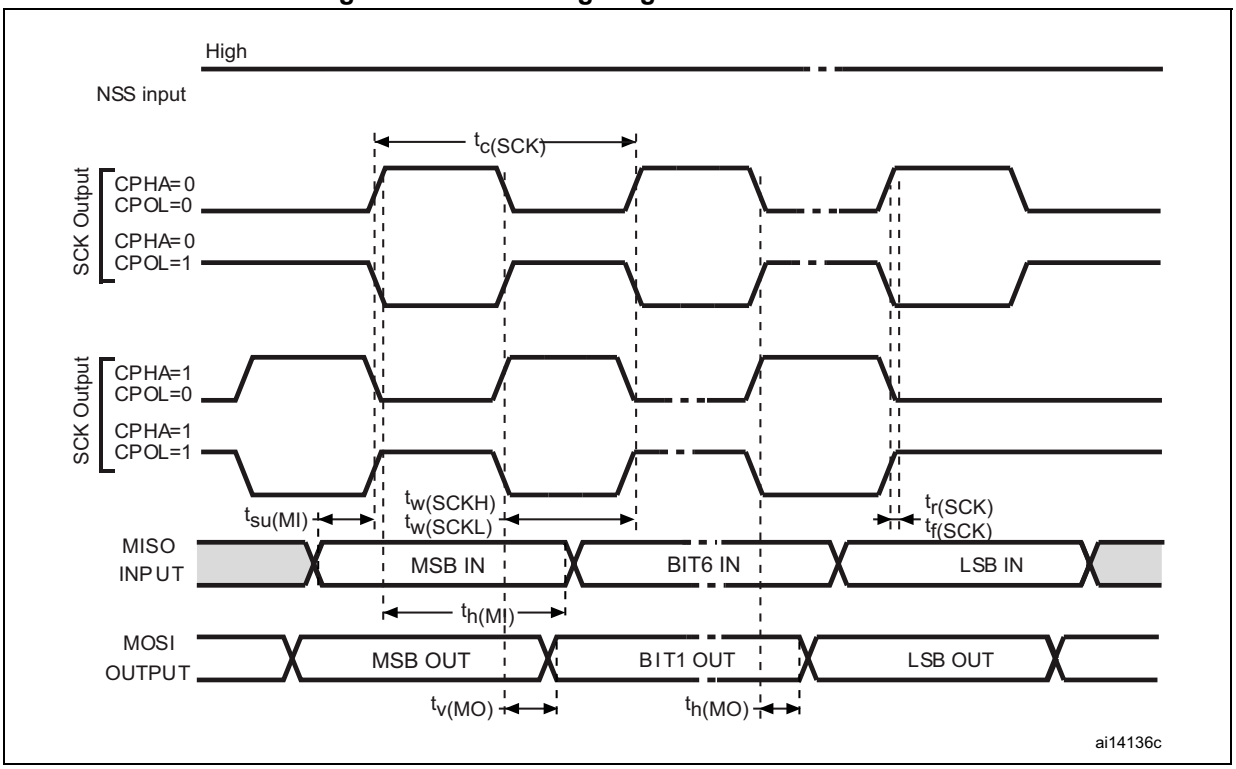
1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

Table 44. Output driving current (PA0 with high sink LED driver capability)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
IR	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +20 mA, V_{DD} = 2.0 V	-	0.45	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

Figure 34. SPI1 timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

I^2C - Inter IC control interface

Subject to general operating conditions for V_{DD}, f_{SYSCLK}, and T_A unless otherwise specified.

The STM8AL I^2C interface (I2C1) meets the requirements of the Standard I^2C communication protocol described in the following table with the restriction mentioned below:

Refer to I/O port characteristics for more details on the input/output alternate function characteristics (SDA and SCL).

Table 47. I^2C characteristics

Symbol	Parameter	Standard mode I^2C		Fast mode I^2C(1)		Unit
		Min(2)	Max (2)	Min (2)	Max (2)	
$t_{w(SCLL)}$	SCL clock low time	4.7	-	1.3	-	µs
$t_{w(SCLH)}$	SCL clock high time	4.0	-	0.6	-	

In the following three tables, data are guaranteed by characterization result, not tested in production.

Table 57. ADC1 accuracy with V_{DDA} = 2.5 V to 3.3 V

Symbol	Parameter	Conditions	Typ.	Max(1)	Unit
DNL	Differential non linearity	f_{ADC} = 16 MHz	1	1.6	LSB
		f_{ADC} = 8 MHz	1	1.6	
		f_{ADC} = 4 MHz	1	1.5	
INL	Integral non linearity	f_{ADC} = 16 MHz	1.2	2	
		f_{ADC} = 8 MHz	1.2	1.8	
		f_{ADC} = 4 MHz	1.2	1.7	
TUE	Total unadjusted error	f_{ADC} = 16 MHz	2.2	3.0	
		f_{ADC} = 8 MHz	1.8	2.5	
		f_{ADC} = 4 MHz	1.8	2.3	
Offset	Offset error	f_{ADC} = 16 MHz	1.5	2	LSB
		f_{ADC} = 8 MHz	1	1.5	
		f_{ADC} = 4 MHz	0.7	1.2	
Gain	Gain error	f_{ADC} = 16 MHz	1	1.5	
		f_{ADC} = 8 MHz			
		f_{ADC} = 4 MHz			

1. Not tested in production.

Table 58. ADC1 accuracy with V_{DDA} = 2.4 V to 3.6 V

Symbol	Parameter	Typ.	Max(1)	Unit
DNL	Differential non linearity	1	2	LSB
INL	Integral non linearity	1.7	3	
TUE	Total unadjusted error	2	4	
Offset	Offset error	1	2	
Gain	Gain error	1.5	3	

1. Not tested in production.

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling two LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC61967-2 which specifies the board and the loading of each pin.

Table 62. EMI data (1)

Symbol	Parameter	Conditions	Monitored frequency band	Max vs.	Unit
				16 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = +25 °C, LQFP32 conforming to IEC61967-2	0.1 MHz to 30 MHz	-3	dBµV
			30 MHz to 130 MHz	9	
			130 MHz to 1 GHz	4	
			EMI Level	2	-

1. Not tested in production.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and charge device model. This test conforms to the ANSI/ESDA/JEDEC JS-001, JESD22-A115 and ANSI/ESD S5.3.1.

Table 63. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value (1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/ JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD S5.3.1	C4B	500	
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine model)	T_A = +25 °C, conforming to JESD22-A115	M2	200	

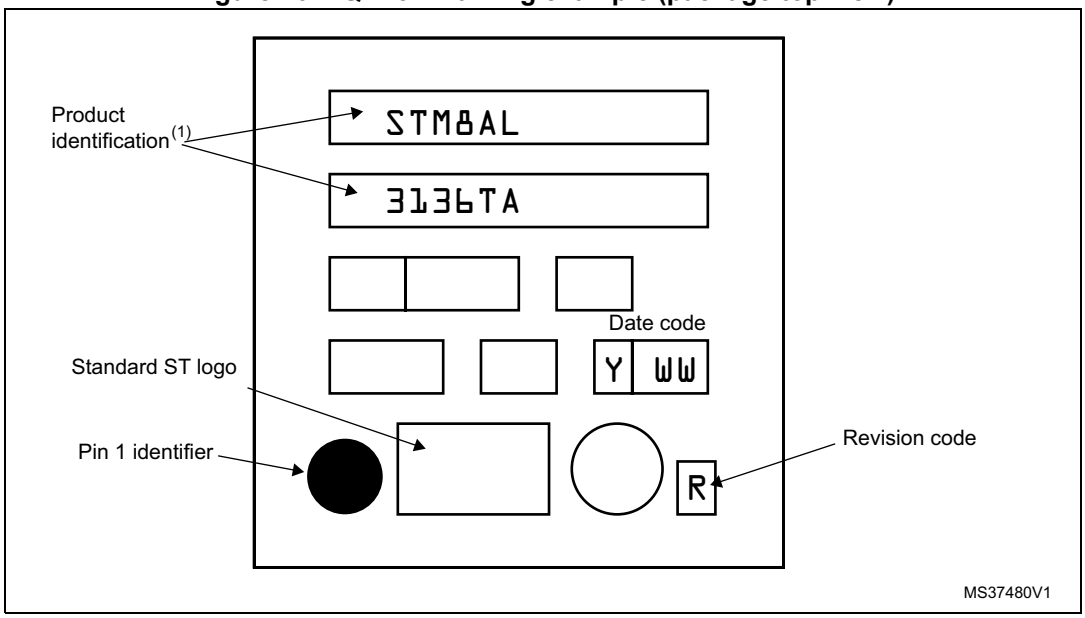
1. Guaranteed by characterization results.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

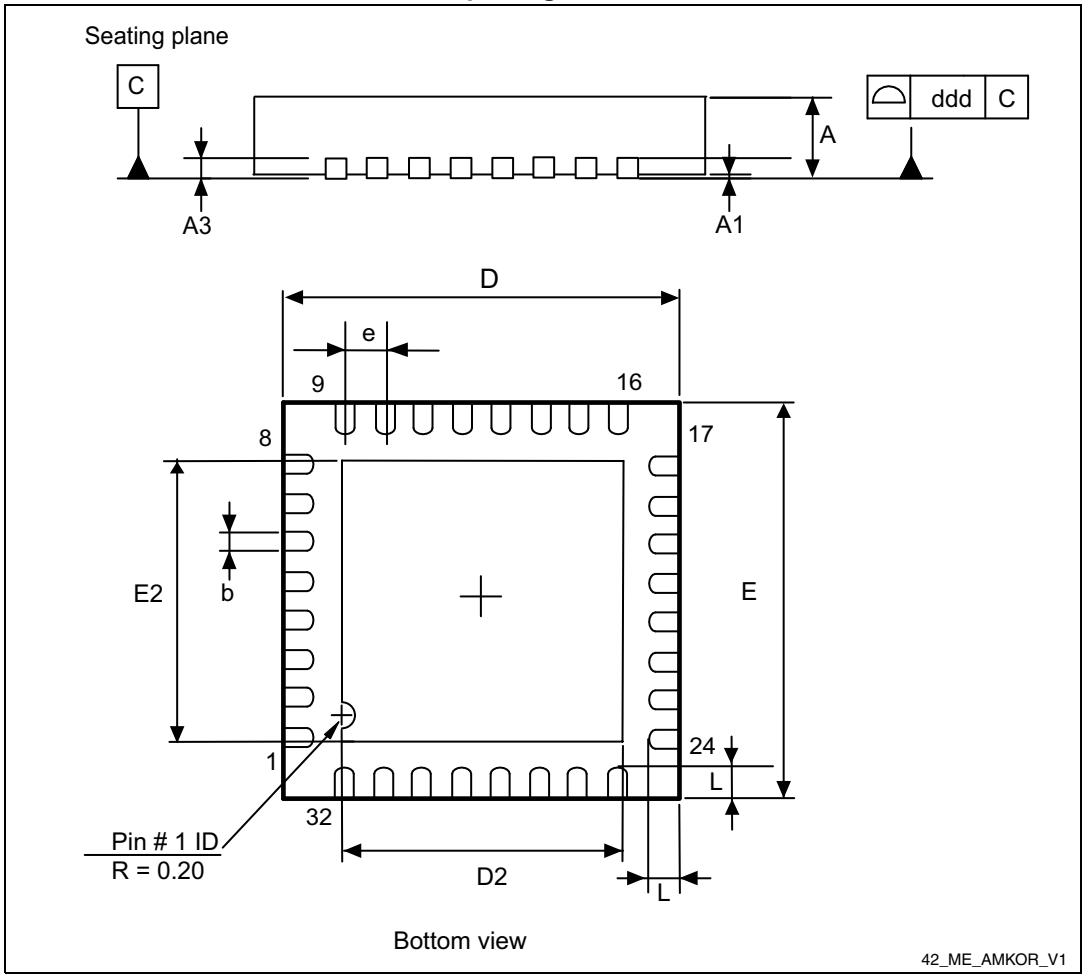
Figure 46. LQFP32 marking example (package top view)



1. Parts marked as “ES” or “E” are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST’s Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

10.4 VFQFPN32 package information

Figure 47. VFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package outline



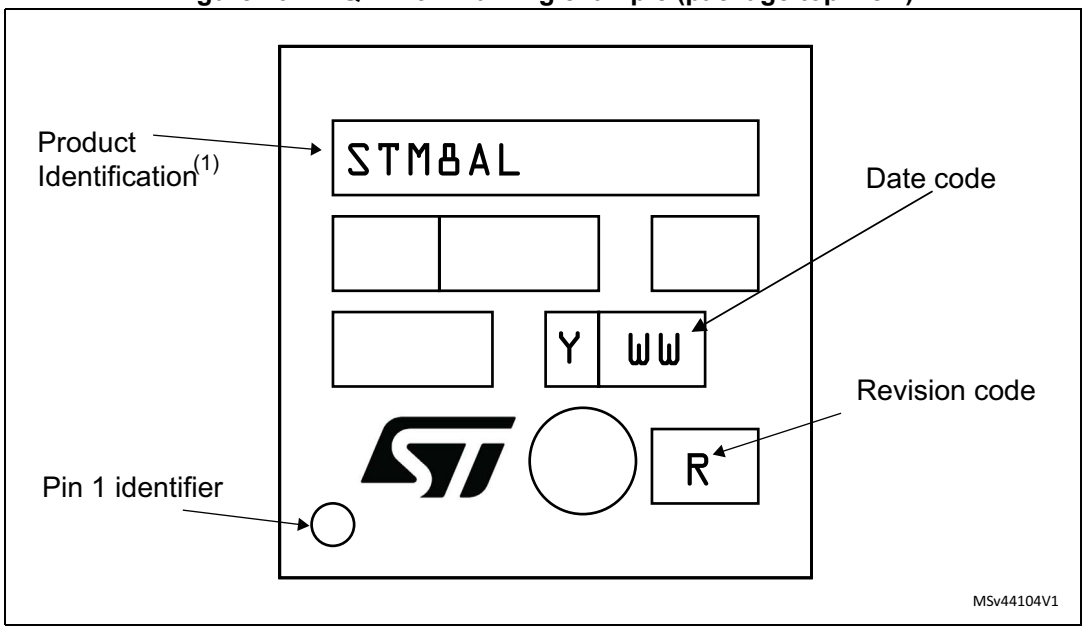
1. Drawing is not to scale.
2. There is an exposed die pad on the underside of the VQFPN package. It is recommended to connect and solder this backside pad to the PCB ground.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 49. VFQFPN32 marking example (package top view)



1. Parts marked as “ES” or “E” are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST’s Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

10.5 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 19: General operating conditions*.

The maximum chip-junction temperature, T_{Jmax}, in degree Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in °C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins
  Where:
  $P_{I/Omax} = \Sigma(V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,

  taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 68. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP48- 7 x 7 mm	65	°C/W
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm	59	
	Thermal resistance junction-ambient VFQFPN32 - 5 x 5 mm	62	

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.